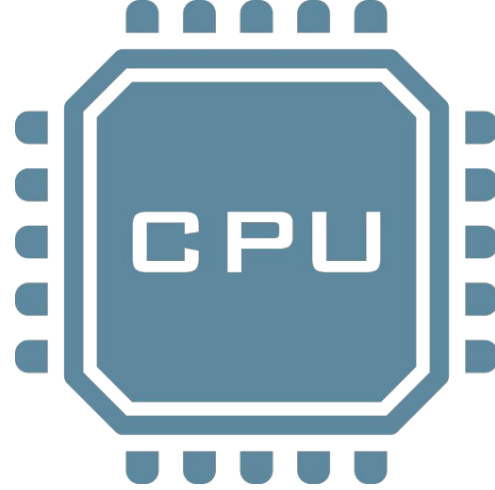
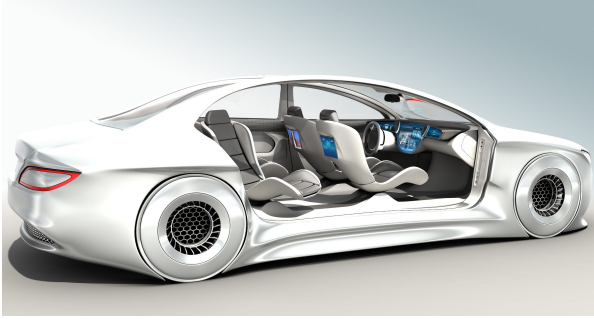


Sıfırdan Bire

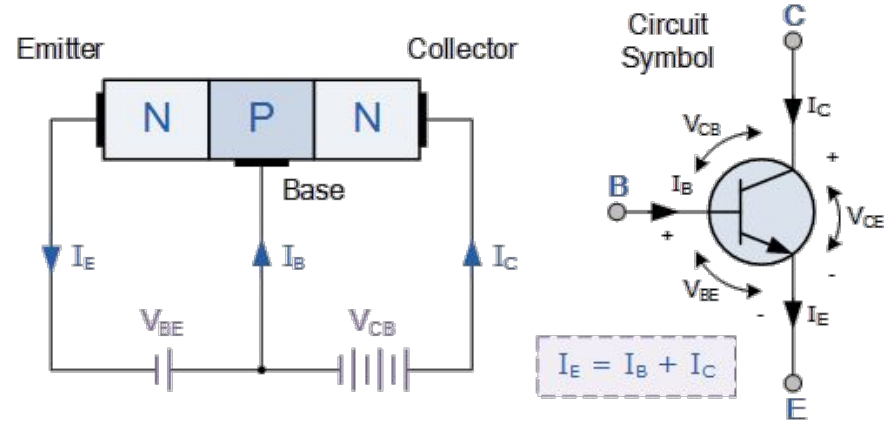
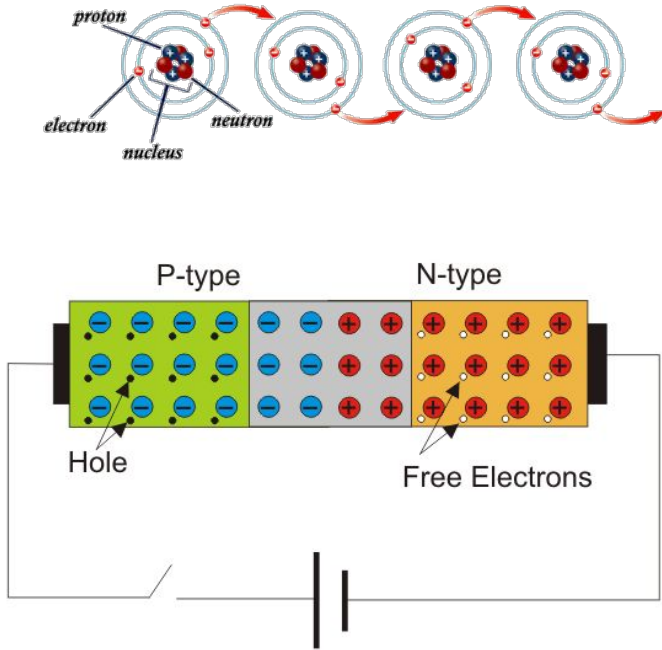


Suhap SAHIN

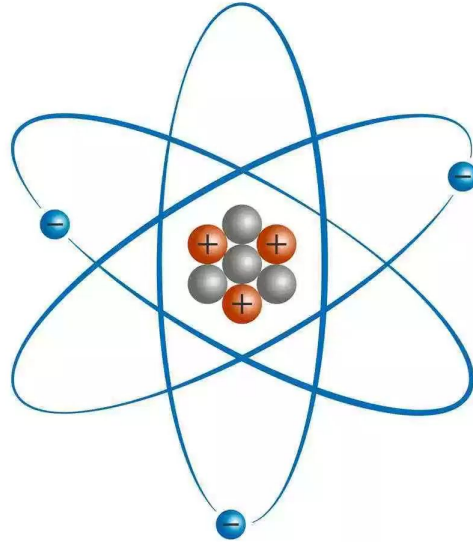
1.1 Mikroislemci Gelismisinin Önemi






1.2 Karmaşıklık Yönetimi



1.2.1 Soyutlama



Atom structure

-  Proton
-  Neutron
-  Electron



Maxwell's Equations

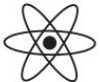
Differential form

$$\nabla \cdot \vec{E} = \frac{\rho}{\epsilon_0}$$

$$\nabla \times \vec{E} = -\frac{\partial \vec{B}}{\partial t}$$

$$\nabla \cdot \vec{B} = 0$$

$$\nabla \times \vec{B} = \mu_0 \vec{J} + \mu_0 \epsilon_0 \frac{\partial \vec{E}}{\partial t}$$



1.2.1 Soyutlama



Resistor



Capacitor



Inductor



Variable Resistor



Transistor

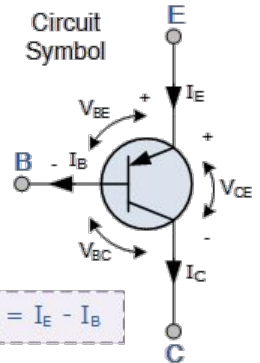
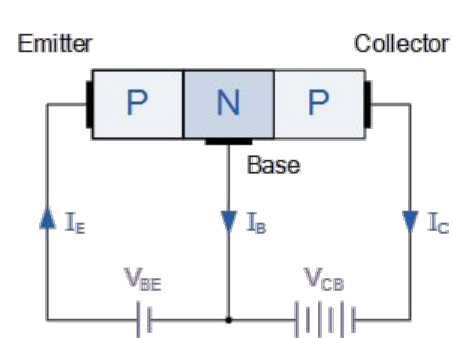
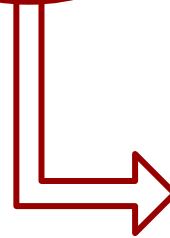


Diode

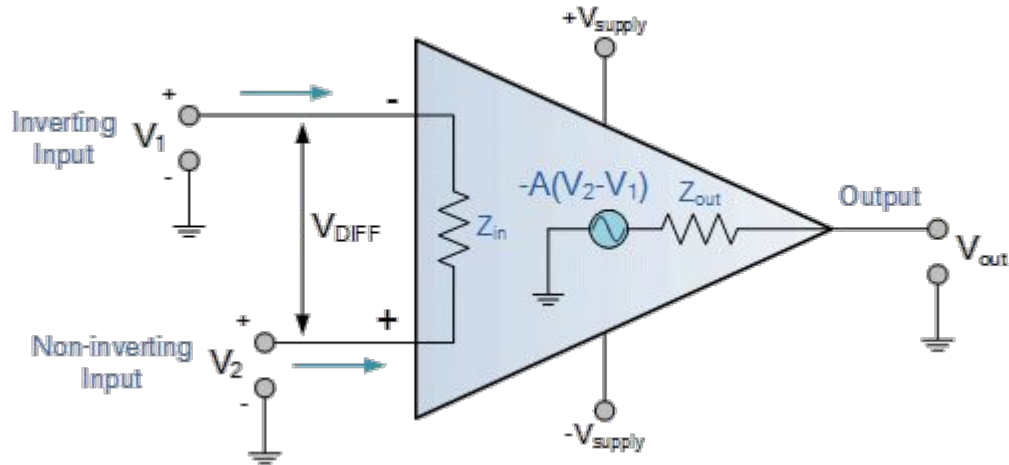
Devices	
Physics	




Transistors
Diodes

Electrons







1.2.1 Soyutlama



Analog Circuits		Amplifiers Filters
Devices		Transistors Diodes
Physics		Electrons

1.2.1 Soyutlama

Digital Circuits	
Analog Circuits	
Devices	
Physics	

AND Gates
NOT Gates

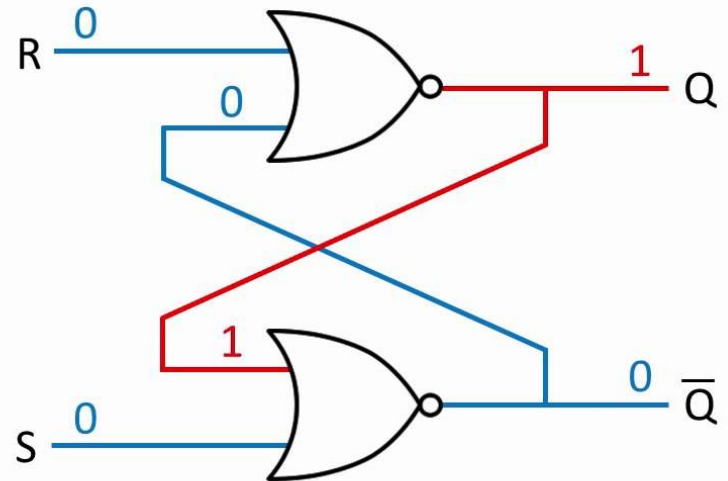
Amplifiers
Filters

Transistors
Diodes

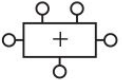

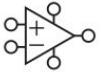


Electrons

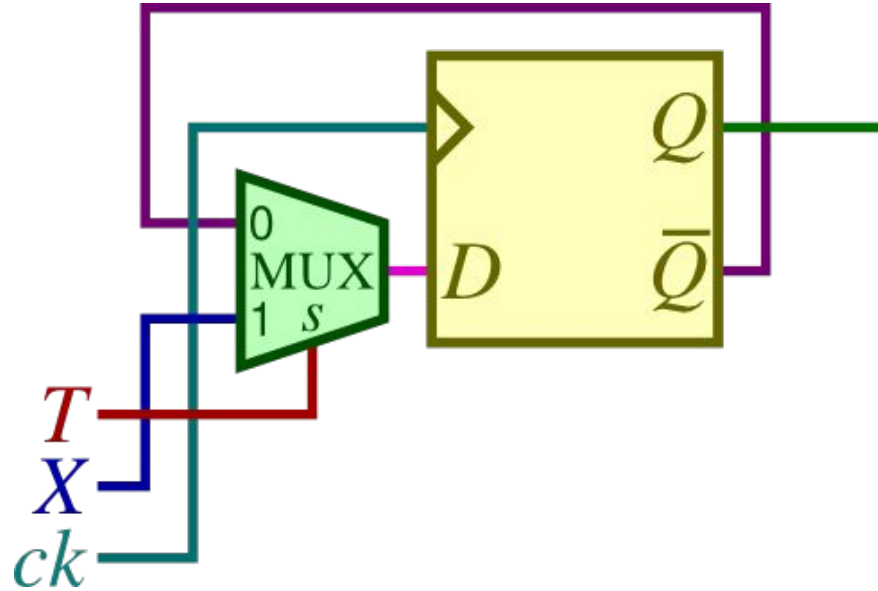
SR Latch

S	R	Q	\bar{Q}
0	0	1	0
0	1	0	1
1	0	1	0
1	1	0	0

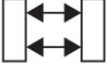
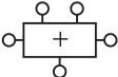

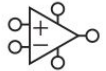




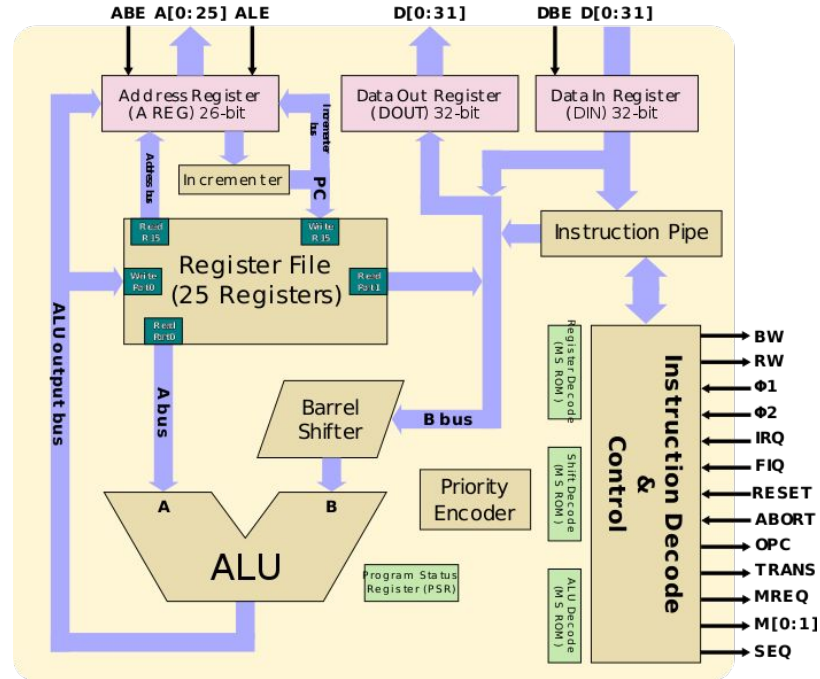
1.2.1 Soyutlama

Logic		Adders Memories
Digital Circuits		AND Gates NOT Gates
Analog Circuits		Amplifiers Filters
Devices		Transistors Diodes
Physics		Electrons


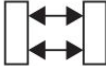
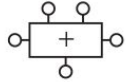

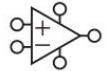




1.2.1 Soyutlama

Micro-architecture		Datapaths Controllers
Logic		Adders Memories
Digital Circuits		AND Gates NOT Gates
Analog Circuits		Amplifiers Filters
Devices		Transistors Diodes
Physics		Electrons



1.2.1 Soyutlama

Architecture		Instructions Registers
Micro-architecture		Datapaths Controllers
Logic		Adders Memories
Digital Circuits		AND Gates NOT Gates
Analog Circuits		Amplifiers Filters
Devices		Transistors Diodes
Physics		Electrons

MIPS32 Instruction Set

Instructions that machine executes

```



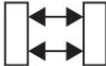
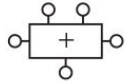
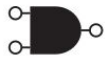
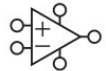


blez $a2, done
move $a7, $zero
li $t4, 99
move $a4, $a1
move $v1, $zero
li $a3, 99
lw $a5, 0($a4)
addiu $a4, $a4, 4
slt $a6, $a5, $a3
movn $v0, $v1, $a6
addiu $v1, $v1, 1
movn $a3, $a5, $a6
    
```

MIPS32 Add Immediate Instruction

001000	00001	00010	0000000101011110
OP Code	Addr 1	Addr 2	Immediate value

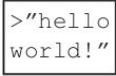


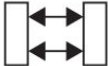
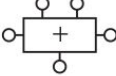

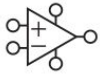


Equivalent mnemonic: **addi** **\$r1**, **\$r2**, **350**

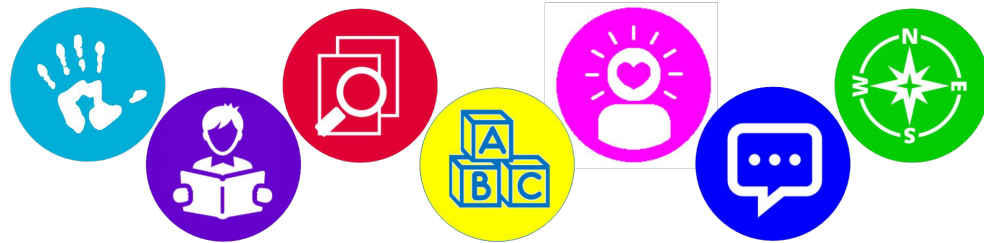
1.2.1 Soyutlama

Operating Systems		Device Drivers
Architecture		Instructions Registers
Micro-architecture		Datapaths Controllers
Logic		Adders Memories
Digital Circuits		AND Gates NOT Gates
Analog Circuits		Amplifiers Filters
Devices		Transistors Diodes
Physics		Electrons



1.2.1 Soyutlama

Application Software		Programs
Operating Systems		Device Drivers
Architecture		Instructions Registers
Micro-architecture		Datapaths Controllers
Logic		Adders Memories
Digital Circuits		AND Gates NOT Gates
Analog Circuits		Amplifiers Filters
Devices		Transistors Diodes
Physics		Electrons

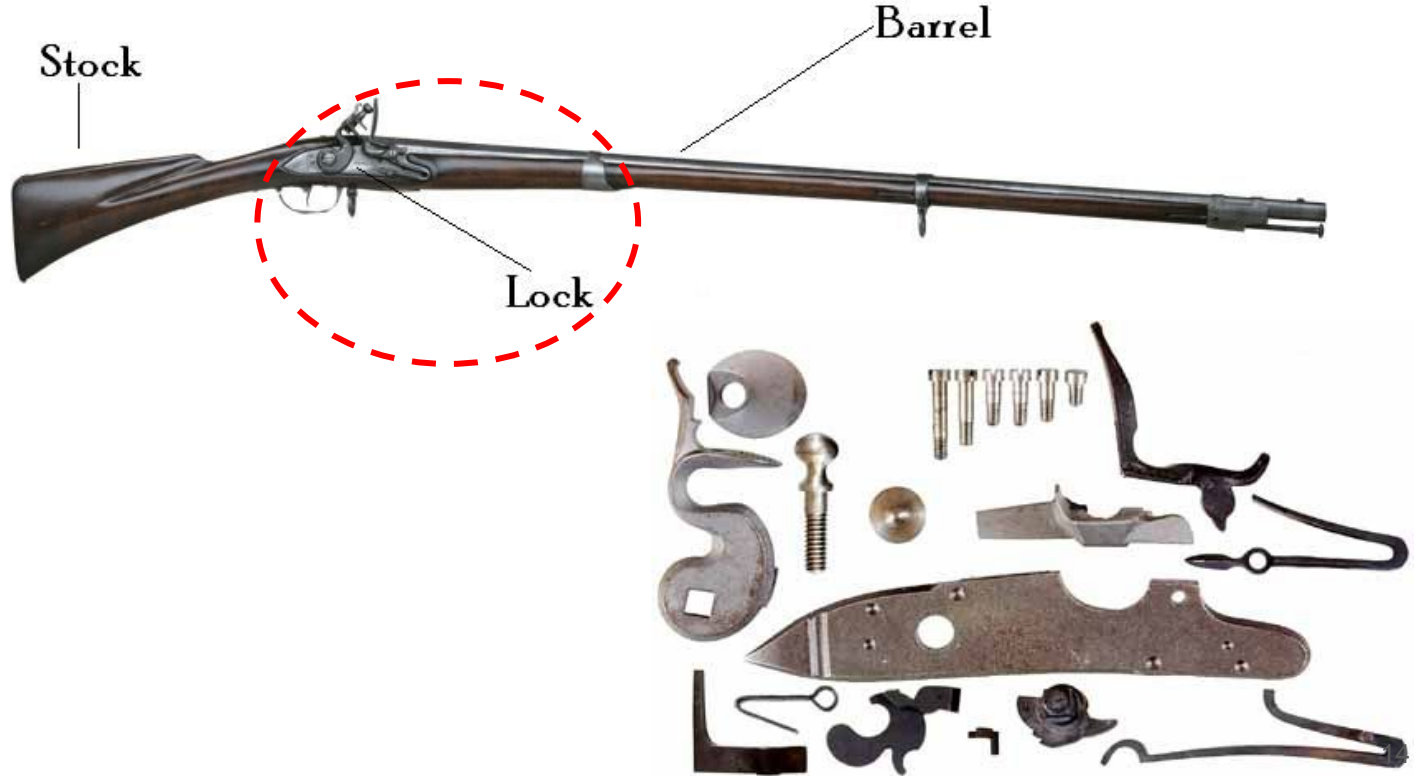


1.2.2 Disiplin



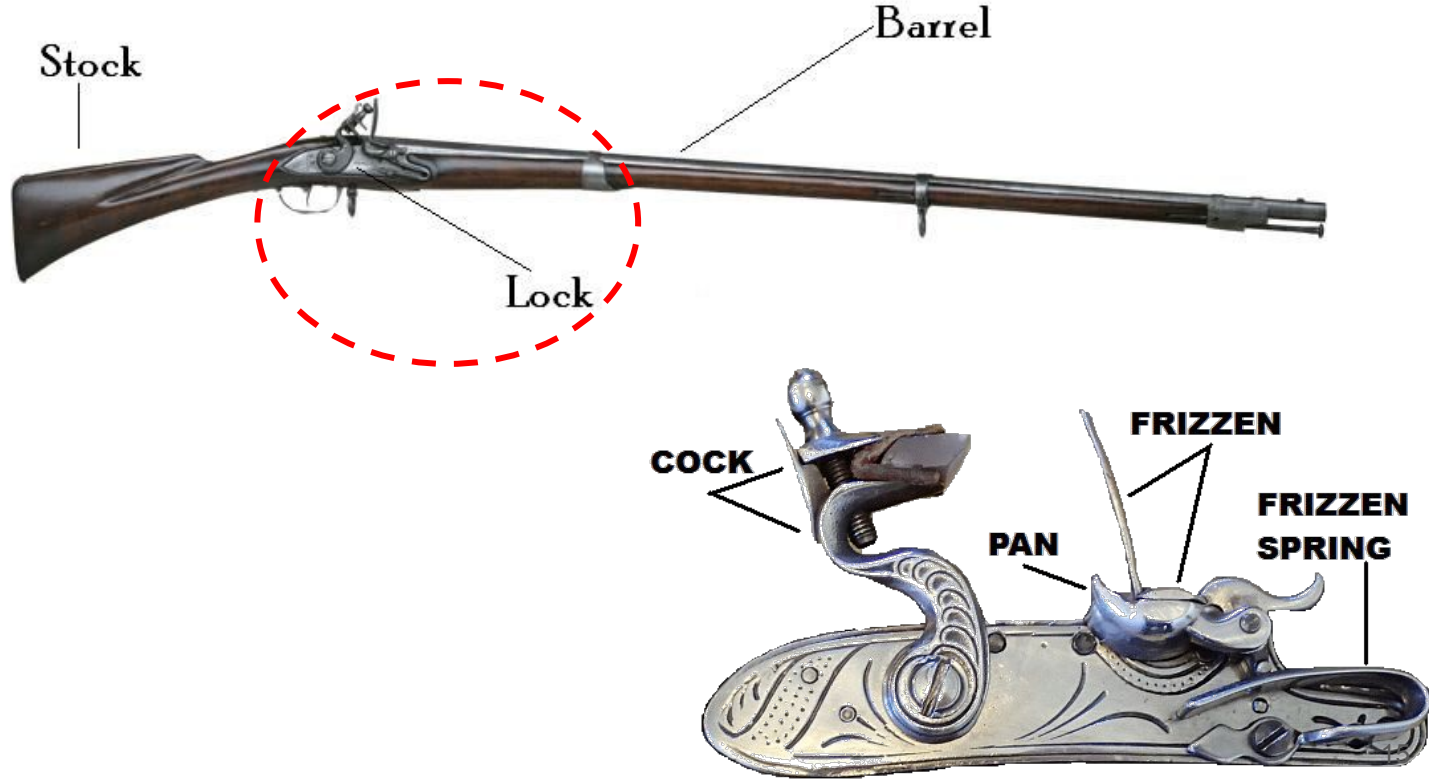
1.2.3 Karmaşıklık için Üc Y

Hierarchy



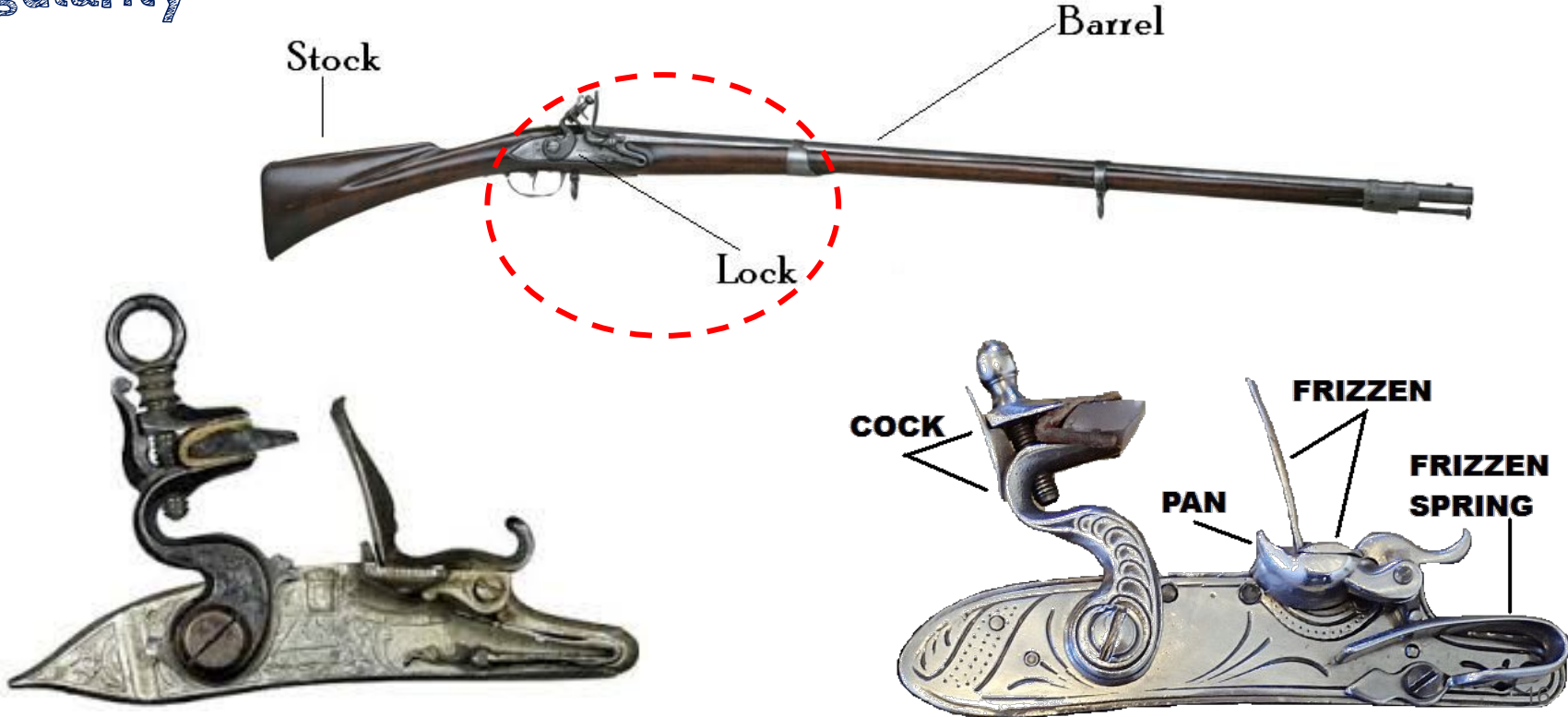
1.2.3 Karmaşıklık için Üc Y

Modularity

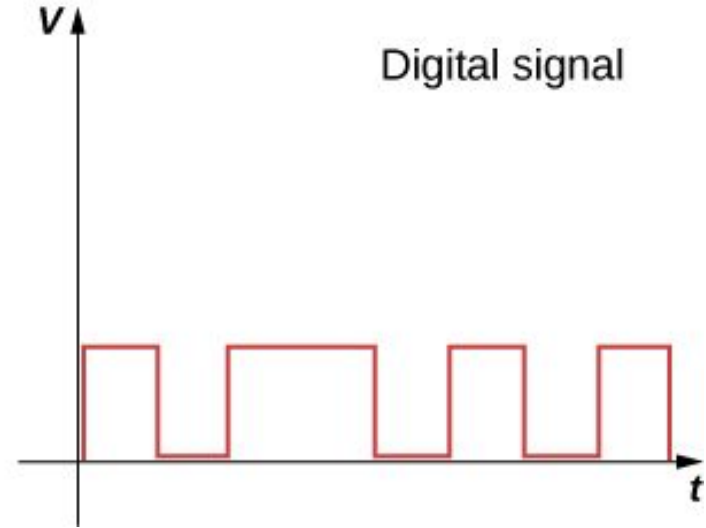
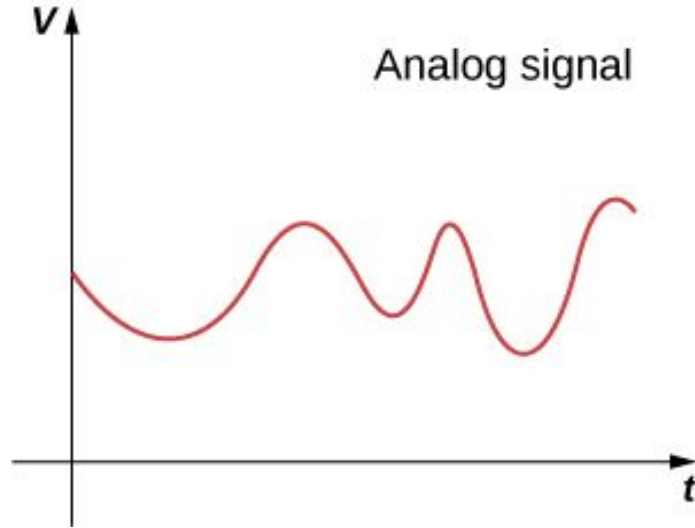


1.2.3 Karmaşıklık için Üc Y

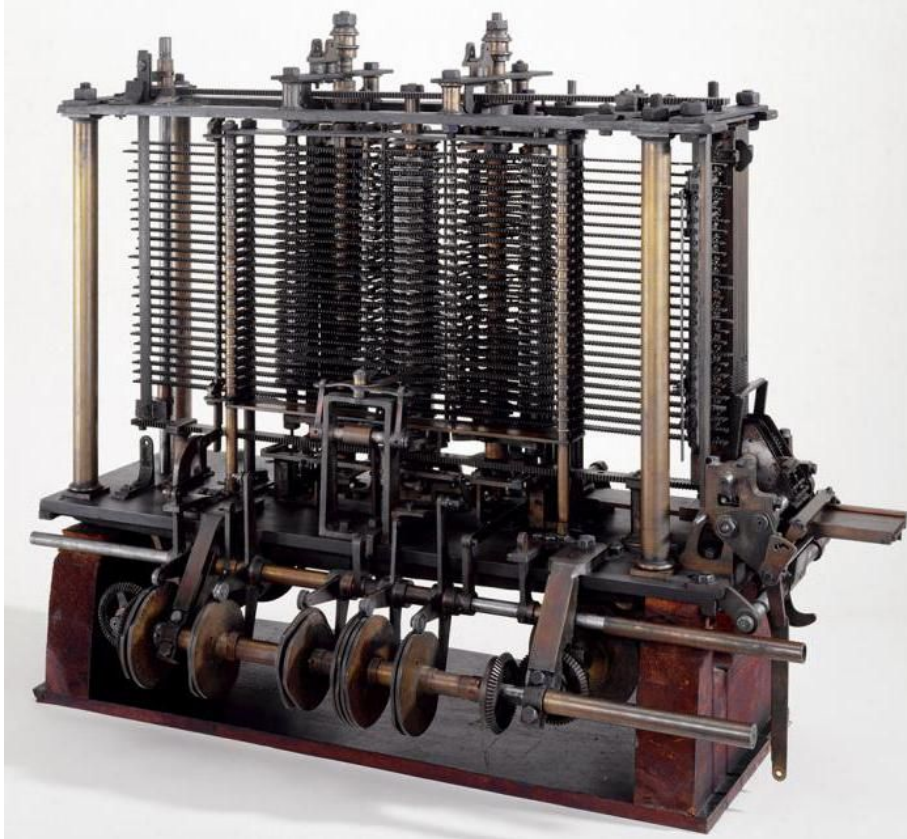
Regularity



1.3 Sayısal Soyutlama



1.3 Sayısal Soyutlama



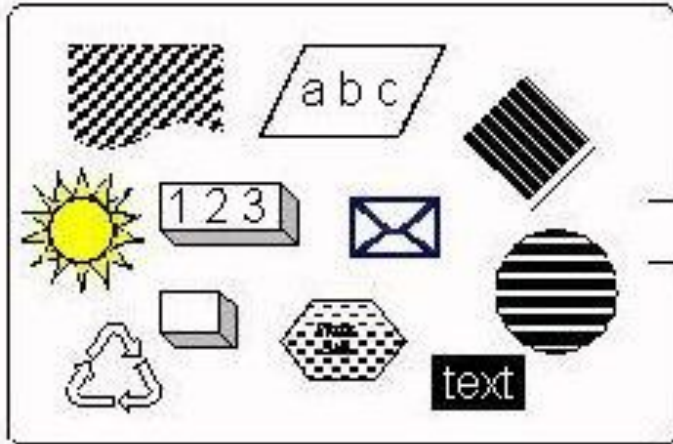
Charles Babbage, 1791-1871
Analytical Engine

0 dan 9 kadar konumlanan disliler

Her bir satır bir basamak
Makinede 25 satır var

1.3 Sayısal Soyutlama

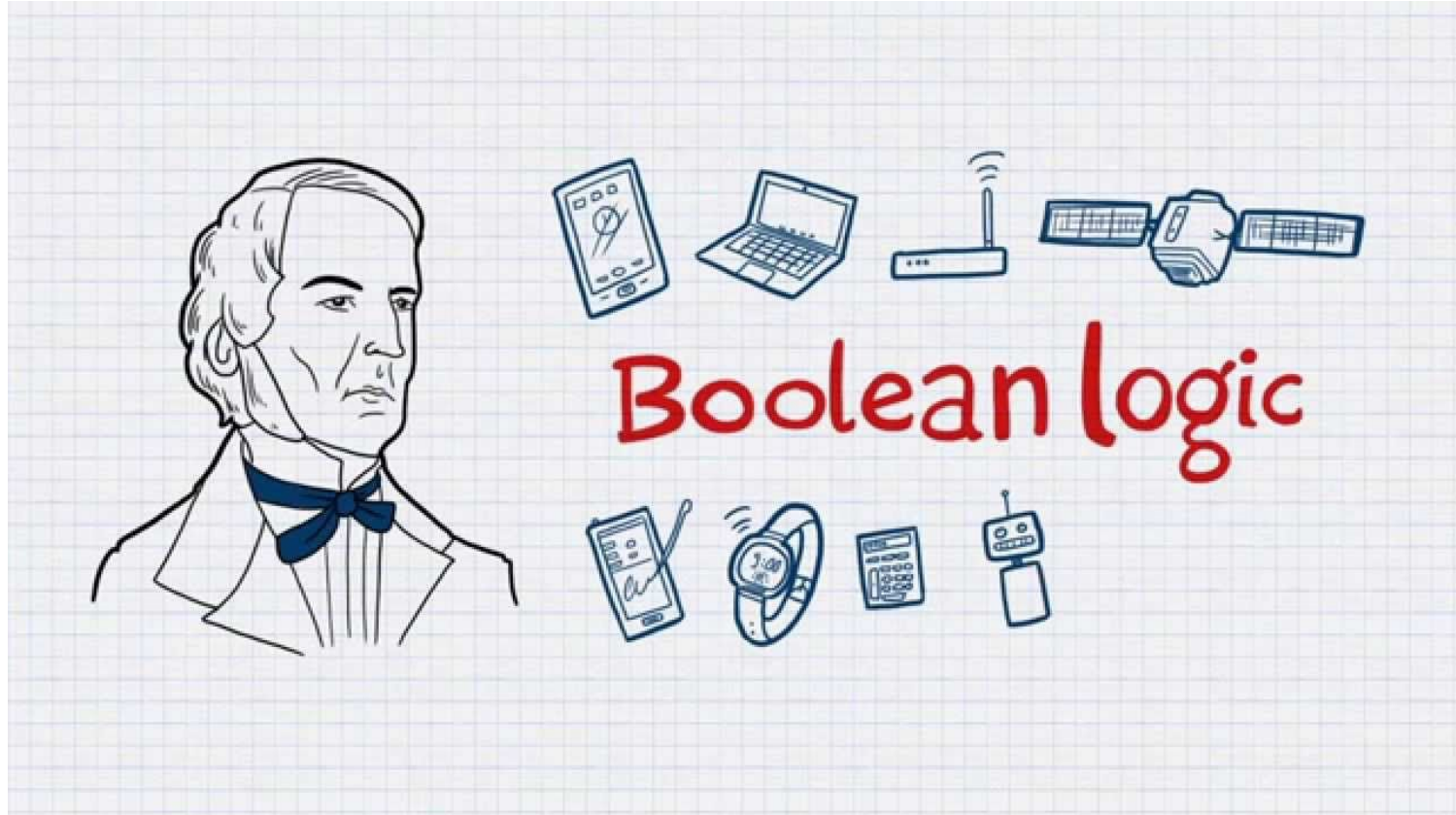
Your Data



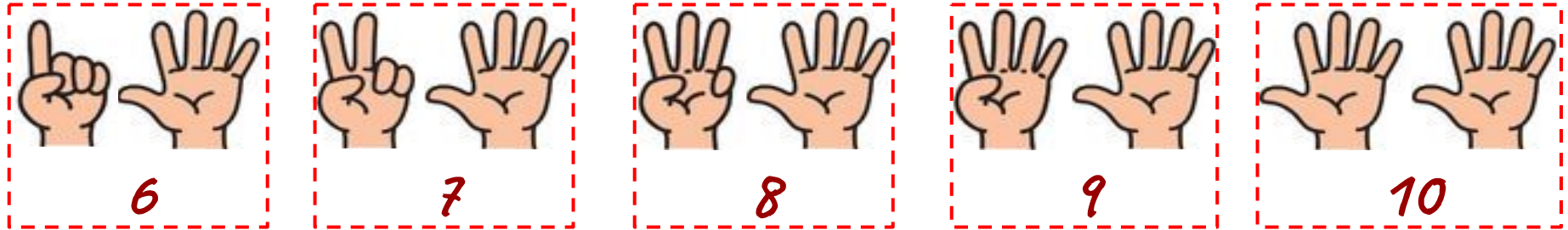
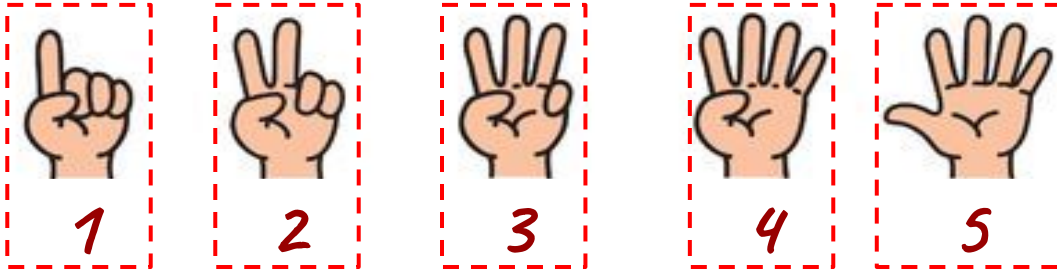
Computer Data

```
01110101011010101
10100101011010101
01010101011010101
01000101011010101
01101010101001100
00101011101100111
10101001010101010
```

1.3 Sayısal Soyutlama



1.4.1 Onluk Sayı Sistemi



1.4.2 ikilik Sistemi

$\overbrace{101100}^{\text{most significant bit}} \underbrace{\quad}_{\text{least significant bit}}$ $\overbrace{\text{DEAFDAD8}}^{\text{most significant byte}} \underbrace{\quad}_{\text{least significant byte}}$

$$84_{10} = (?)_2$$

$$84_{10} = (1010100)_2$$

$$84 \geq 64$$

1

$$20 < 32$$

0

$$20 \geq 16$$

1

$$4 < 8$$

0

$$4 \geq 4$$

1

$$0 < 2$$

0

$$0 < 1$$

0

1.4.3 Onaltılık Sayı Sistemi

Hexadecimal Sayı Sistemi

1's column
16's column
256's column

$$2ED_{16} = \underset{\substack{\text{two} \\ \text{two hundred} \\ \text{fifty six's}}}{2} \times 16^2 + \underset{\substack{\text{fourteen} \\ \text{sixteens}}}{E} \times 16^1 + \underset{\substack{\text{thirteen} \\ \text{ones}}}{D} \times 16^0 = 749_{10}$$

Hexadecimal Digit	Decimal Equivalent	Binary Equivalent
0	0	0000
1	1	0001
2	2	0010
3	3	0011
4	4	0100
5	5	0101
6	6	0110
7	7	0111
8	8	1000
9	9	1001
A	10	1010
B	11	1011
C	12	1100
D	13	1101
E	14	1110
F	15	1111

1.4.3 Onaltılık Sayı Sistemi

Hexadecimal Sayı Sistemi

$$(1111010)_2 = (?)_{16}$$

$$(1111010)_2 = (0111\ 1010)_2$$

$$(0111\ 1010)_2 = (7A)_{16}$$

1.4.3 Onaltılık Sayı Sistemi

Hexadecimal Sayı Sistemi

$$333_{10} = (?)_{16}$$

$$333_{10} = (14D)_{16}$$

$$333 \geq 256$$

1

$$77 < 16$$

4

$$13 \geq 1$$

D

1.4.4 Bytes, Nibbles

Byte : 8 bit

Nibble : 4 bit

Word : işlemci mimarisine bağlı

64 bit işlemci → 64 bit word

1.4.4 Bytes, Nibbles

$$2^{10} = 1024 \approx 10^3$$

$$2^{10} (10^3) = 1 \text{ Kilobit (1KB)}$$

$$2^{20} (10^6) = 1 \text{ Megabit (1MB)}$$

$$2^{30} (10^9) = 1 \text{ Gigabit (1GB)}$$

$$2^{24} = ?$$

$$2^{24} = 2^{20} 2^4$$

$$2^{20} \times 2^4 = 2^4 \times 1 \text{ milyon}$$

$$2^4 \times 1 \text{ milyon} = 16 \text{ milyon}$$

1.4.5 ikilik Toplama

$$\begin{array}{r} 11 \\ 4277 \\ + 5499 \\ \hline 9776 \end{array}$$

← carries →

$$\begin{array}{r} 11 \\ 1011 \\ + 0011 \\ \hline 1110 \end{array}$$

Tasma

$$\begin{array}{r} 111 \\ 1101 \\ + 0101 \\ \hline 10010 \end{array}$$

Tasma



1996 yılında fırlatılan Ariane 5 roketi(7 milyar dolar); fırlatılmasından 40 saniye sonra patladı.

Roketi kontrol eden bilgisayar 16 bitlik işlem sınırını aştı ve çöktü.

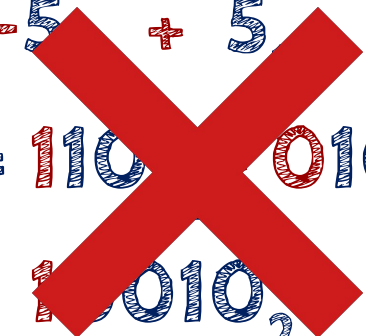
Aynı bilgiyarda aynı kod Ariane 4 roketi kullanılarak defalarca test edildi.

Ancak Ariane 5, daha hızlı bir motora sahipti

1.4.6 işaret/büyüklik sayıları

$$+5_{10} = 0101_2$$

$$-5_{10} = 1101_2$$


$$\begin{aligned} -5_{10} + 5_{10} \\ = 1101_2 + 0101_2 \\ = 10010_2 \end{aligned}$$


$$-0_{10} = 1000_2$$

$$+0_{10} = 0000_2$$

2'ye tümleyen sayılar

$$+2_{10} = 0010_2$$

$$\begin{aligned} -2_{10} &= 0010_2 \\ &= 1101_2 \\ &= 1101_2 + 1_2 \\ &= 1110_2 \end{aligned}$$

2'ye tümleyen sayılar

4bit isaretsiz sayılar

16 deger: $0 \rightarrow 15$

4bit ikiye tümleyen sayılar

16 deger: $-8 \rightarrow 7$ (0 pozitif)

N bit ikiye tümleyen sayılar

2^N deger: $-2^{N-1} \rightarrow 2^{N-1} - 1$

toplama

$$\begin{aligned} & \text{---} 2_{10} + 1_{10} \\ & = 1110_2 + 0001_2 \\ & = 1111_2 \\ & = \text{---} 1_{10} \end{aligned}$$

$$\begin{aligned} & \text{---} 7_{10} + 7_{10} \\ & = 1001_2 + 0111_2 \\ & = 10000_2 \\ & = 0000_2 \\ & = 0_{10} \end{aligned}$$

cikarma

$$\begin{aligned} & 5_{10} - 3_{10} \\ &= 5_2 + (-3_{10}) \\ &= 0101_2 + 1101_2 \\ &= 0010_{10} \\ &= 2_2 \end{aligned}$$

$$\begin{aligned} & + 3_{10} = 0011_2 \\ & 1100_2 + 0001_2 \\ & - 3_{10} = 1101_2 \end{aligned}$$

Tasma



Pozitif + Pozitif = Negatif
Negatif + Negatif = Pozitif

Tasma



4bit ikiye tümleyen sayılar

16 deger: $-8 \rightarrow 7$ (0 pozitif)

$$+4_{10} + 5_{10}$$

$$= 0100_2 + 0101_2$$

$$= 1001_2$$

$$= -7_{10}$$

isaret düzenleme

$$+3_{10} = 0011_2$$

$$-3_{10} = 1101_2$$

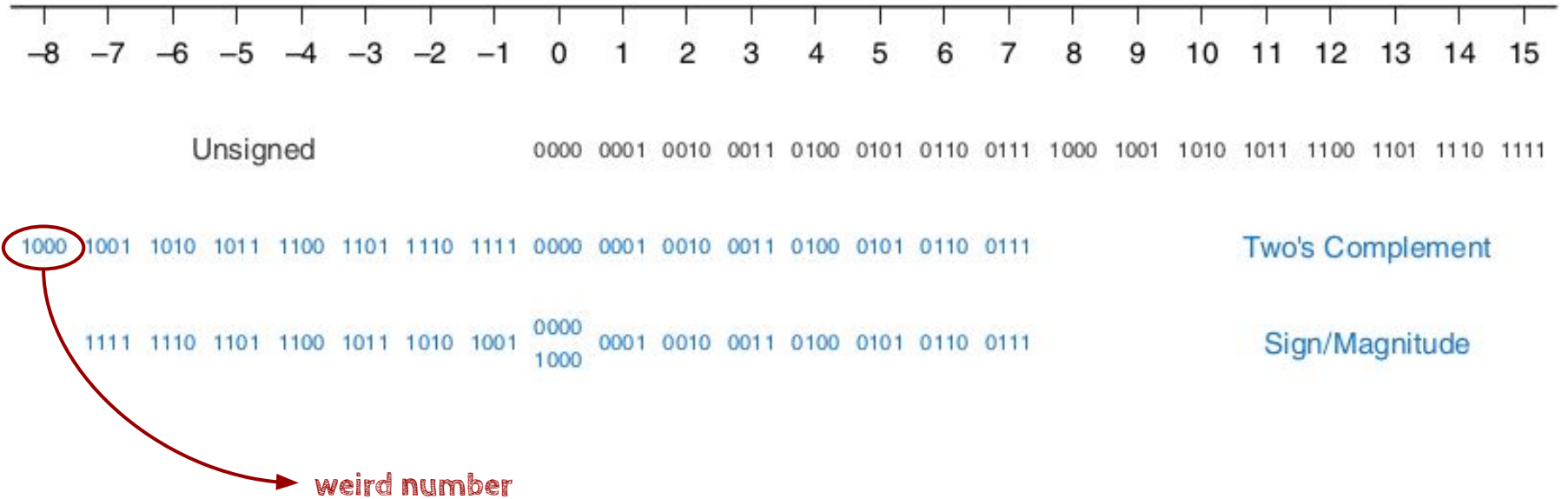
$$+3_{10} = 000011_2$$

$$-3_{10} = 111101_2$$

Karsilastırma

System	Range
Unsigned	$[0, 2^N - 1]$
Sign/Magnitude	$[-2^{N-1} + 1, 2^{N-1} - 1]$
Two's Complement	$[-2^{N-1}, 2^{N-1} - 1]$

Karsilastirma



Lojik Kapılar

NOT

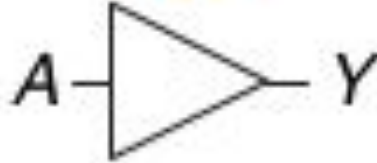


$$Y = \bar{A}$$

A	Y
0	1
1	0

Lojik Kapılar

BUF



$$Y = A$$

A	Y
0	0
1	1

Lojik Kapılar

AND



$$Y = AB$$

A	B	Y
0	0	0
0	1	0
1	0	0
1	1	1

Lojik Kapılar

OR



$$Y = A + B$$

A	B	Y
0	0	0
0	1	1
1	0	1
1	1	1

Lojik Kapılar

XOR



$$Y = A \oplus B$$

A	B	Y
0	0	0
0	1	1
1	0	1
1	1	0

NAND



$$Y = \overline{AB}$$

A	B	Y
0	0	1
0	1	1
1	0	1
1	1	0

NOR

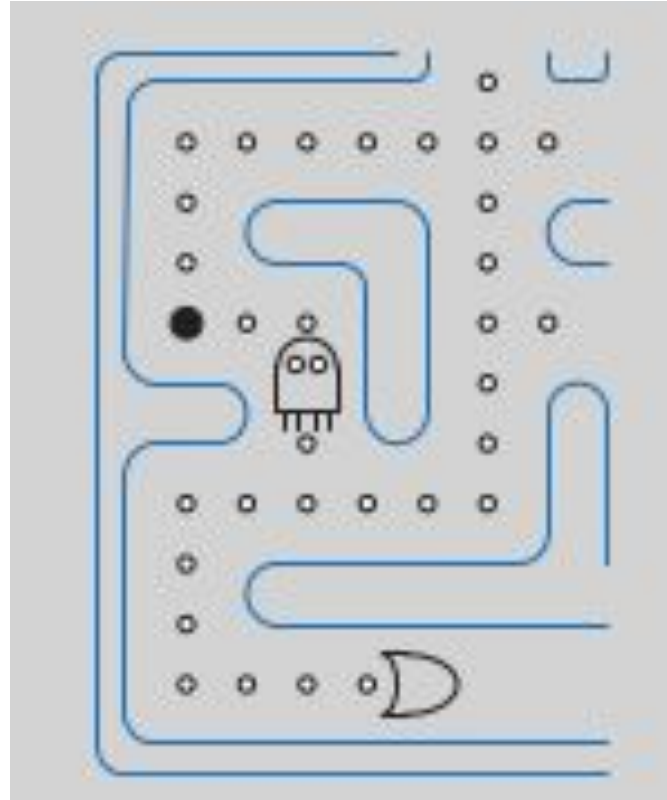


$$Y = \overline{A+B}$$

A	B	Y
0	0	1
0	1	0
1	0	0
1	1	0

Lojik Kapılar

A silly way to remember the OR symbol is that its input side is curved like Pacman's mouth, so the gate is hungry and willing to eat any TRUE inputs it can find!



Lojik Kapılar

XNOR



$$Y = \overline{A \oplus B}$$

A	B	Y
0	0	1
0	1	0
1	0	0
1	1	1

A	B	Y
0	0	1
0	1	0
1	0	0
1	1	1

Lojik Kapılar

NOR3



$$Y = \overline{A + B + C}$$

A	B	C	Y
0	0	0	1
0	0	1	0
0	1	0	0
0	1	1	0
1	0	0	0
1	0	1	0
1	1	0	0
1	1	1	0

A	B	C	Y
0	0	0	1
0	0	1	0
0	1	0	0
0	1	1	0
1	0	0	0
1	0	1	0
1	1	0	0
1	1	1	0

Dijital Soyutlamaya yakından bakış

$0\text{ V} \rightarrow A = 0$; $5\text{ V} \rightarrow A = 1$ olarak yorumlansın

Sistemler az miktarda gürültüyü tolere edebilirler:

$4.97\text{ V} \rightarrow A = 1$ olarak yorumlanır.

Ancak

$4.3\text{ V}?$

$2.8\text{ V}?$

$2.500000\text{ V}?$

Besleme Gerilimi

Sistemdeki en düşük voltaj, toprak(GND)= 0 V

Sistemdeki en yüksek voltaj, VDD=(1970 & 1980) =5V

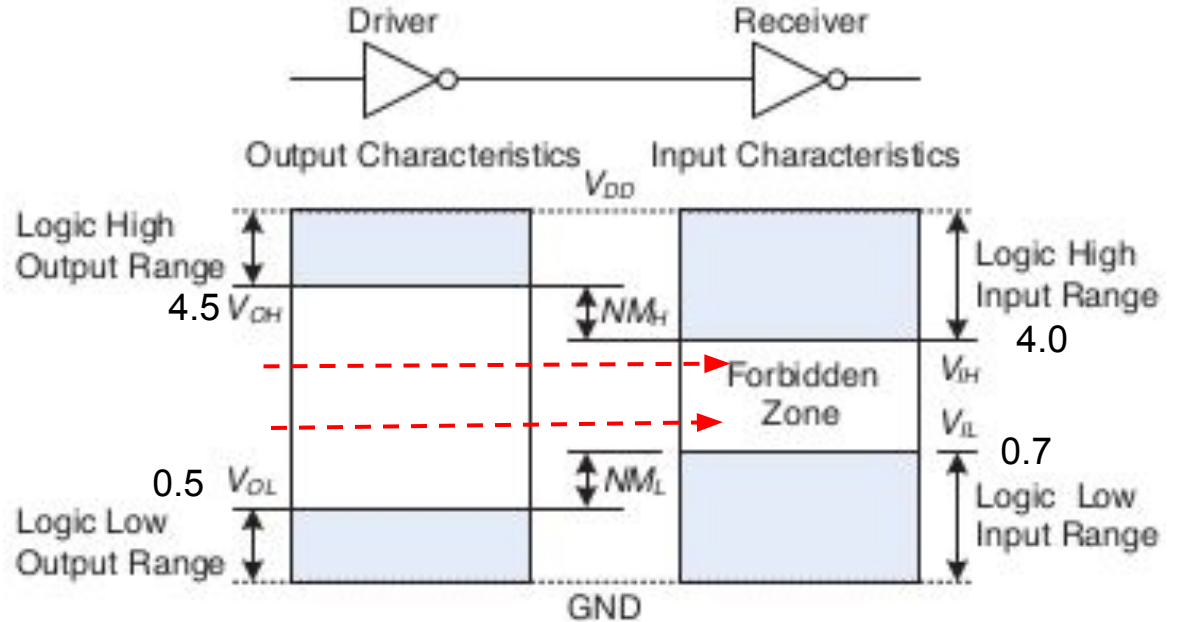
Transistörler küçükdükçe(güç tasarrufu ve aşırı yüklenme);
VDD= 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V düştü.

Lojik Seviye

$$\begin{array}{l} V_{OL} < V_{IL} \\ V_{OH} > V_{IH} \end{array}$$

$$NM_L = V_{IL} - V_{OL}$$

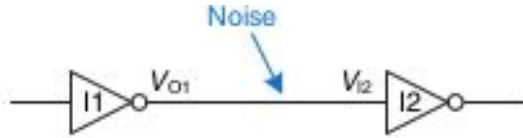
$$NM_H = V_{OH} - V_{IH}$$



Gürültü Aralığı

Interterlerin en yüksek ve en düşük gürültü sınırı nedir?

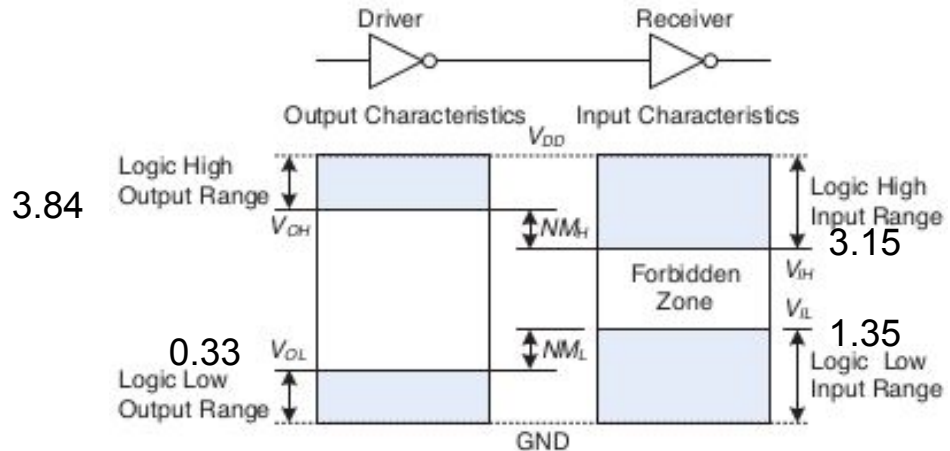
Devre V_{O1} ve V_{I2} arasındaki 1V'lık gürültüyü tolere edebilir mi?



$$\begin{aligned}V_{DD} &= 5V \\V_{IL} &= 1.35V \\V_{IH} &= 3.15V \\V_{OL} &= 0.33V \\V_{OH} &= 3.84V\end{aligned}$$

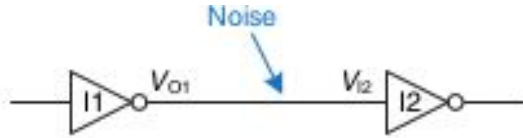
$$NM_L = V_{IL} - V_{OL}$$

$$NM_H = V_{OH} - V_{IH}$$



Gürültü Aralığı

Interterlerin en yüksek ve en düşük gürültü sınırı nedir?



$$V_{DD} = 5V$$

$$V_{IL} = 1.35V$$

$$V_{IH} = 3.15V$$

$$V_{OL} = 0.33V$$

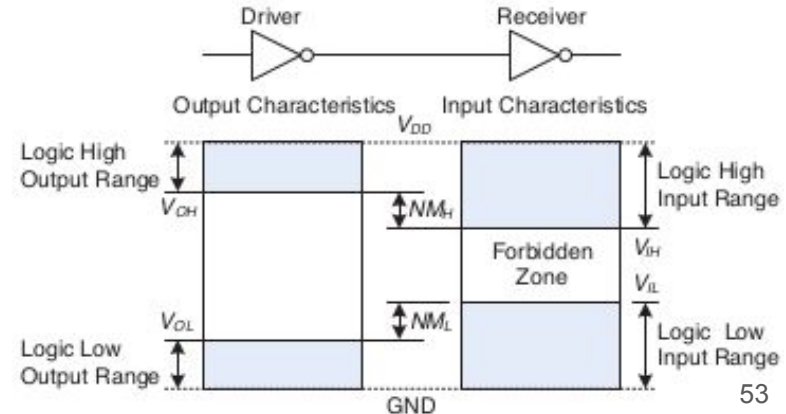
$$V_{OH} = 3.84V$$

$$\begin{aligned} NM_L &= V_{IL} - V_{OL} \\ &= 1.35V - 0.33V \\ &= 1.02V \end{aligned}$$

$$\begin{aligned} NM_H &= V_{OH} - V_{IH} \\ &= 3.84V - 3.15V \\ &= 0.69V \end{aligned}$$

$$NM_L = V_{IL} - V_{OL}$$

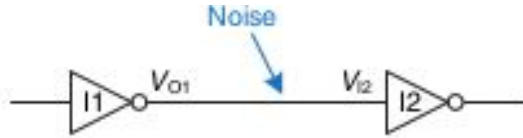
$$NM_H = V_{OH} - V_{IH}$$



Lojik Seviye- Gürültü Aralığı

Interterlerin en yüksek ve en düşük gürültü sınırı nedir?

Devre V_{O1} ve V_{I2} arasındaki 1V'lık gürültüyü tolere edebilir mi?



$$V_{DD} = 5V$$

$$V_{IL} = 1.35V$$

$$V_{IH} = 3.15V$$

$$V_{OL} = 0.33V$$

$$V_{OH} = 3.84V$$

LOW

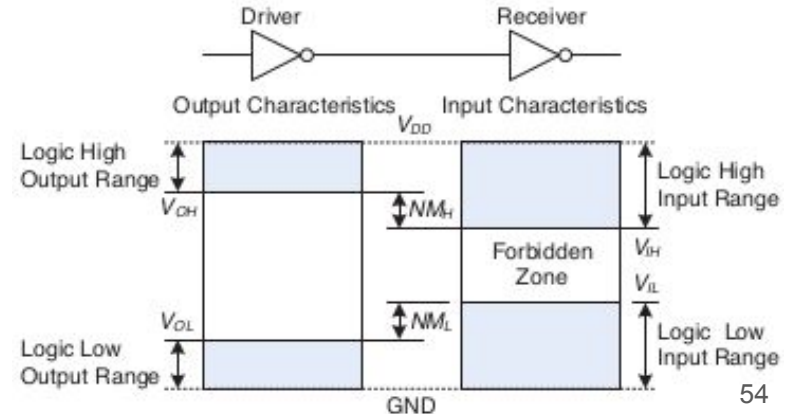
$$NM_L = 1.02V$$

HIGH

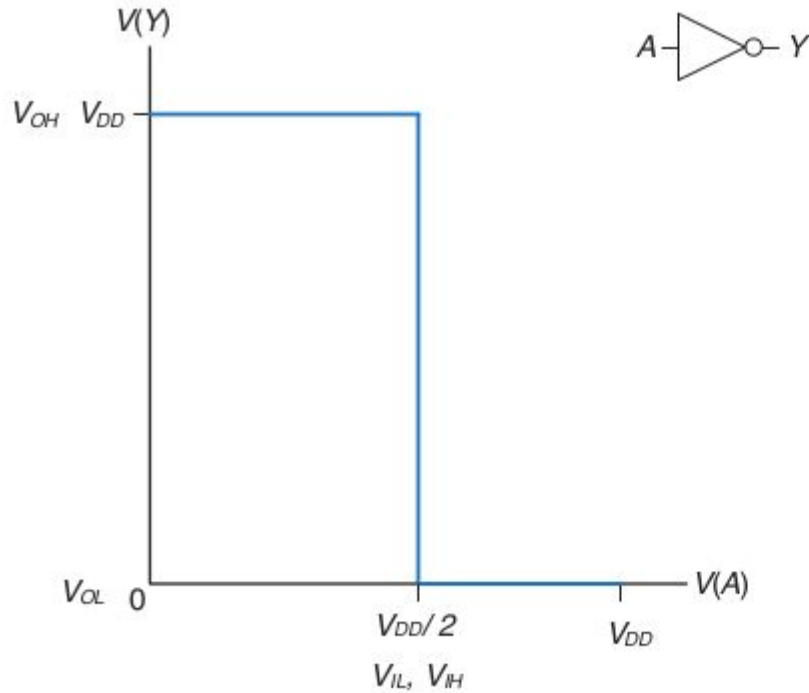
$$NM_H = 0.69V$$

$$NM_L = V_{IL} - V_{OL}$$

$$NM_H = V_{OH} - V_{IH}$$



DC iletim karakteristigi



$$V(A) < V_{DD}/2 \Rightarrow V(Y) = V_{DD}$$

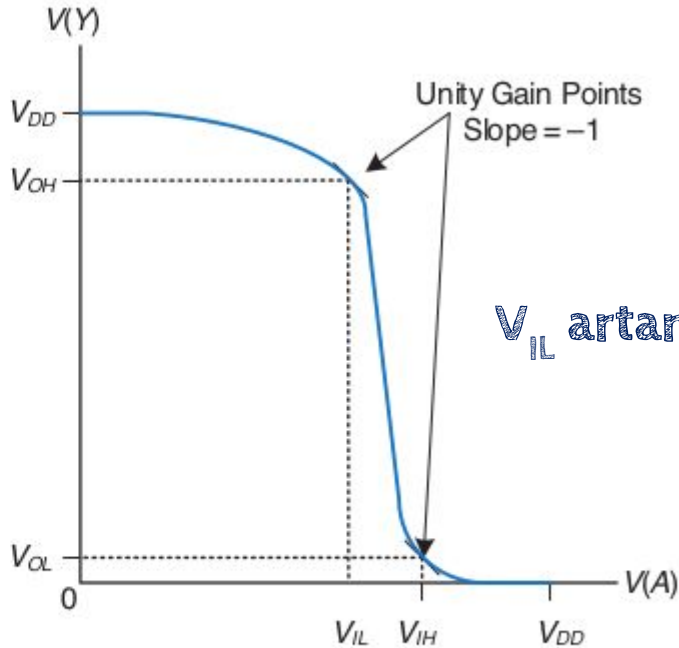
$$V(A) > V_{DD}/2 \Rightarrow V(Y) = 0$$

$$V_{IL} = V_{IH} = V_{DD}/2$$

$$V_{OH} = V_{DD}$$

$$V_{OL} = 0$$

DC iletim karakteristigi



V_{IL} artarsa V_{OH} azalır

$$\begin{array}{ll} V(A) = 0 & V(Y) = V_{DD} \\ V(A) > V_{DD} & V(Y) = 0 \end{array}$$

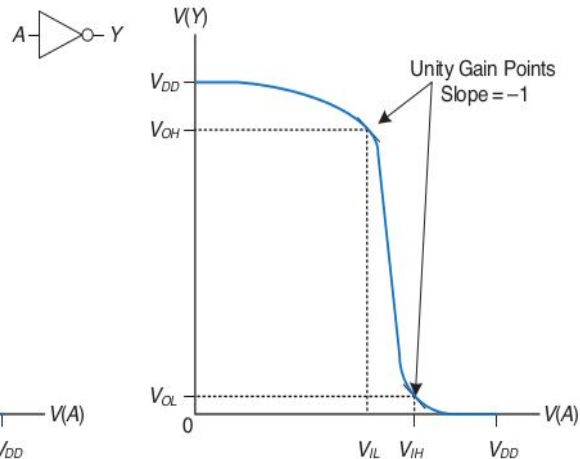
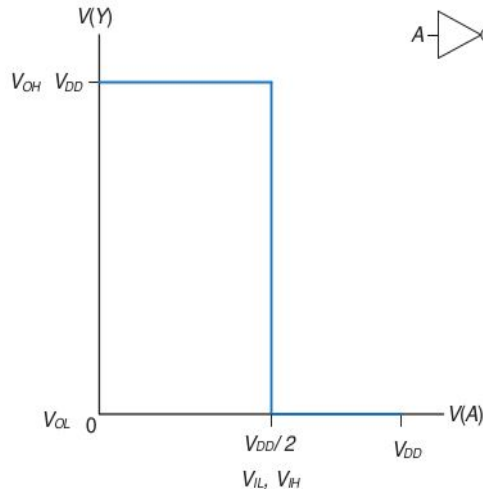
Unity Gain Points:
 $dV(Y) / dV(A) = -1$

Lojik seviyeleri (0 yada 1) UGP noktaları olarak belirlemek sistemin gürültü toleransını en üst seviyeye çıkaracaktır.

Static displin

Dört büyük Lojik aile (70 ~ 90):

- Transistör-Transistör Logic (TTL)
- Complementary Metal-Oxide-Semiconductor Logic (CMOS)
- Low Voltage TTL Logic (LVTTTL)
- Low Voltage CMOS Logic (LVCMOS)



Static disciplin

Logic Family	V_{DD}	V_{IL}	V_{IH}	V_{OL}	V_{OH}
TTL	5 (4.75–5.25)	0.8	2.0	0.4	2.4
CMOS	5 (4.5–6)	1.35	3.15	0.33	3.84
LVTTL	3.3 (3–3.6)	0.8	2.0	0.4	2.4
LVC MOS	3.3 (3–3.6)	0.9	1.8	0.36	2.7

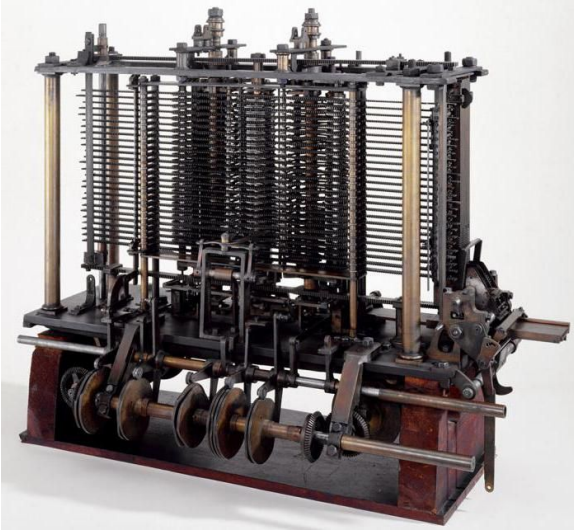
Static disciplin

		Receiver			
		TTL	CMOS	LVTTL	LVC MOS
Driver	TTL	OK	NO: $V_{OH} < V_{IH}$	MAYBE ^a	MAYBE ^a
	CMOS	OK	OK	MAYBE ^a	MAYBE ^a
	LVTTL	OK	NO: $V_{OH} < V_{IH}$	OK	OK
	LVC MOS	OK	NO: $V_{OH} < V_{IH}$	OK	OK

^a As long as a 5 V HIGH level does not damage the receiver input

CMOS Transistorler

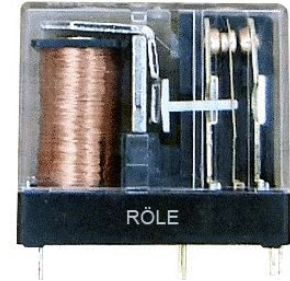
Babbage Analytical Engine



vakum tüp



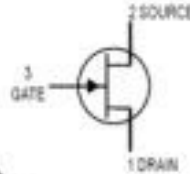
röle



CMOS Transistorler

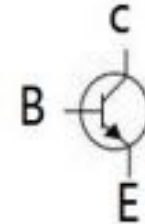
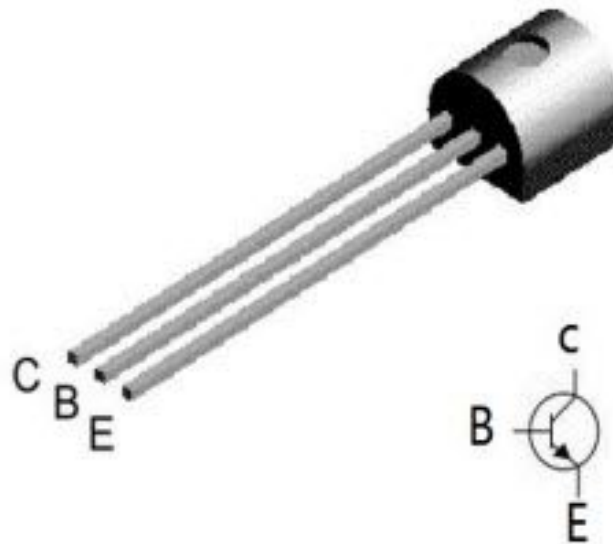
MOSFET

(metal-oxide-semiconductor field effect transistor)

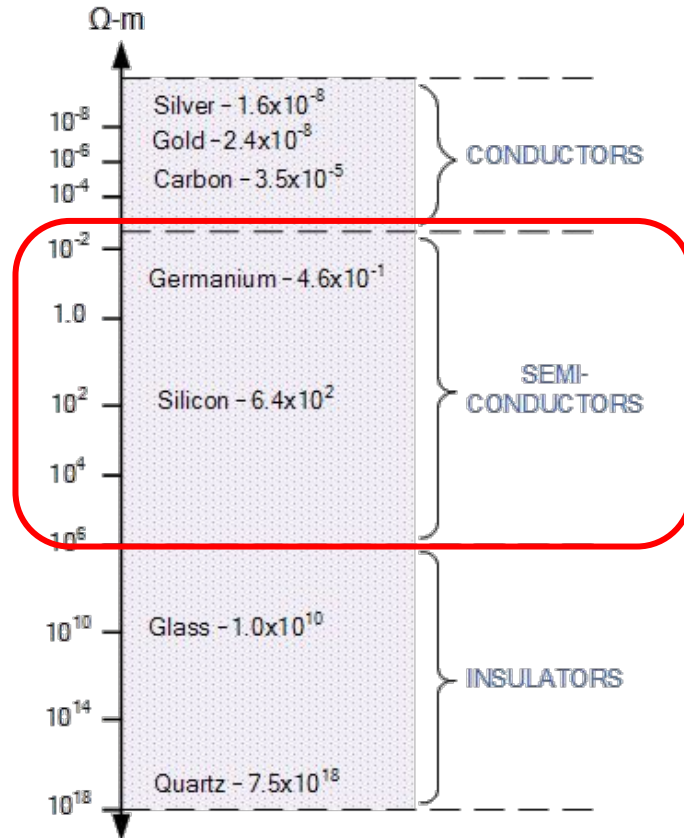


BJT

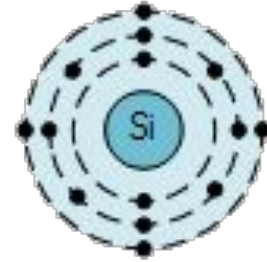
(bipolar junction transistor)



Yarıiletgenler



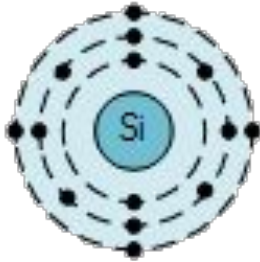
A Silicon Atom,
Atomic number = "14"



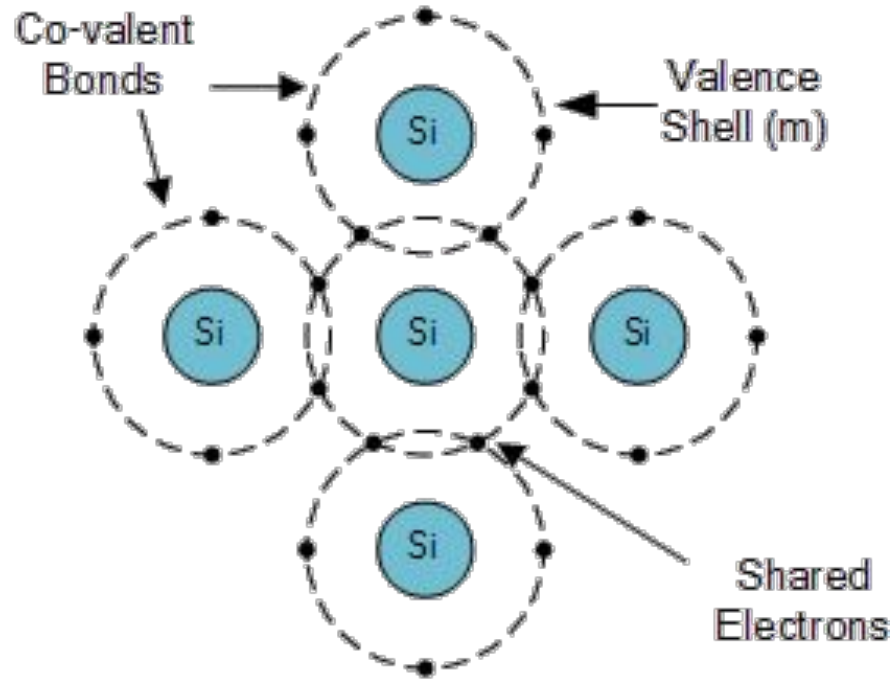
Silicon atom showing
4 electrons in its outer
valence shell (m)

Yarıiletkenler

A Silicon Atom,
Atomic number = "14"



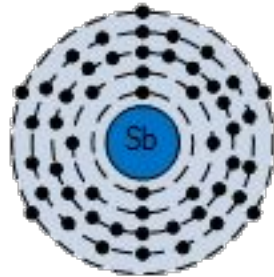
Silicon atom showing
4 electrons in its outer
valence shell (m)



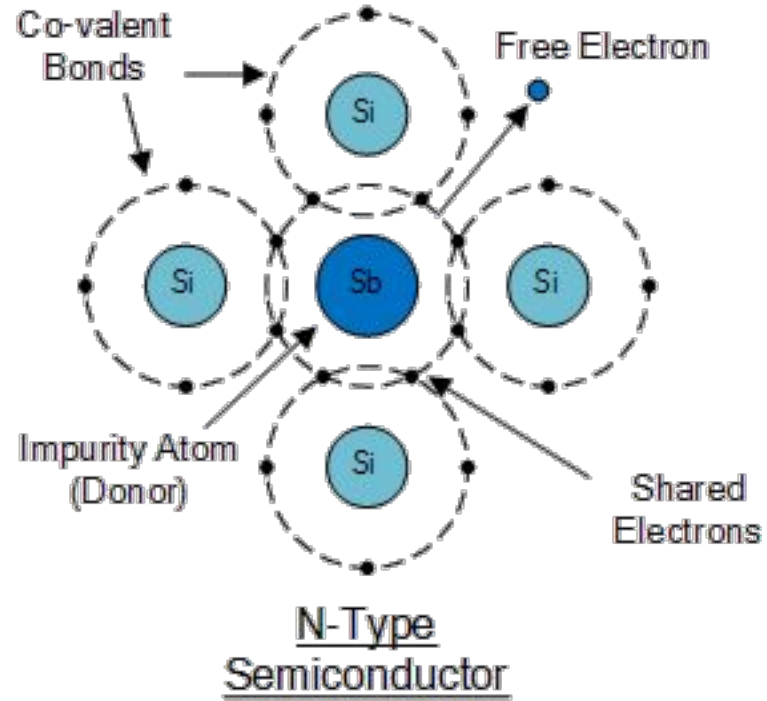
Silicon Crystal Lattice

Yarıiletkenler

An Antimony Atom,
Atomic number = "51"



Antimony atom showing
5 electrons in its outer
valence shell (o)

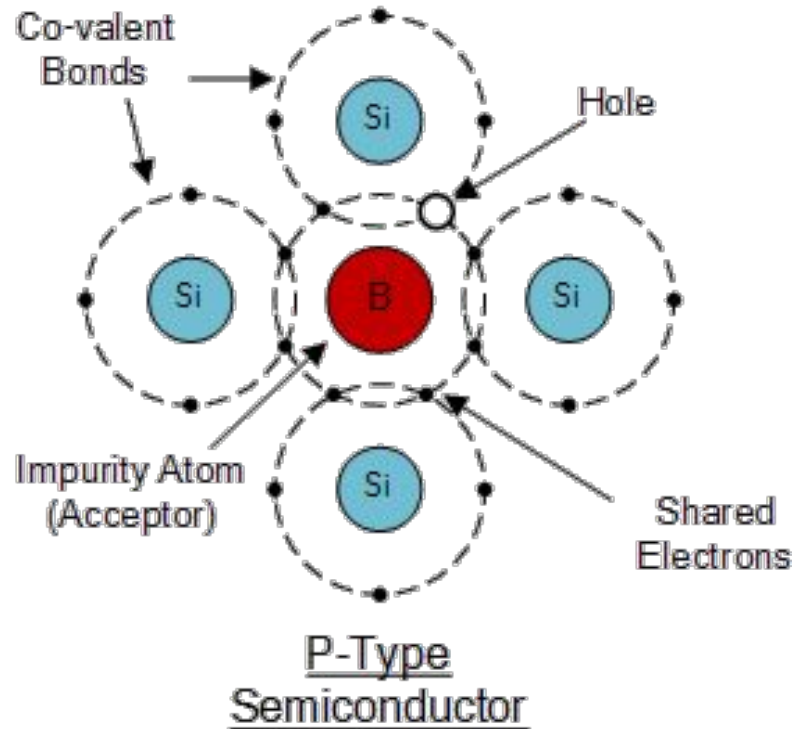


Yarıiletkenler

A Boron Atom,
Atomic number = "5"

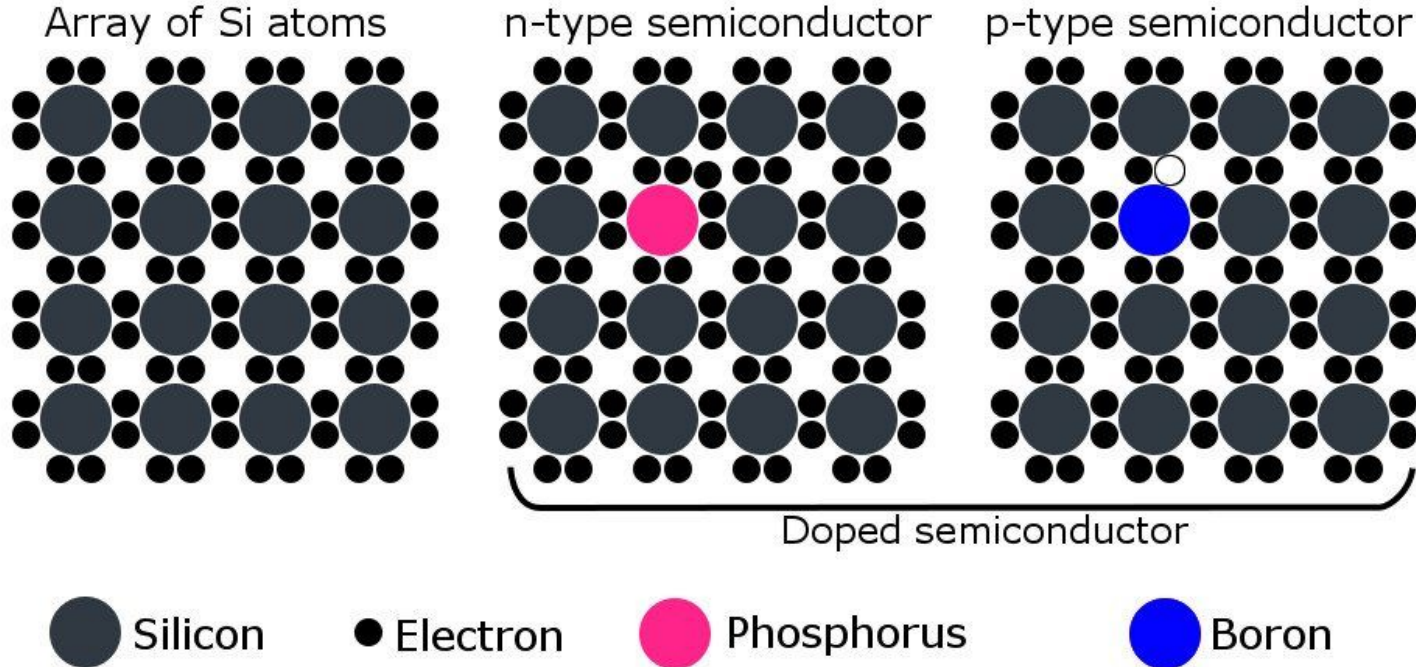


Boron atom showing
3 electrons in its outer
valence shell (L)

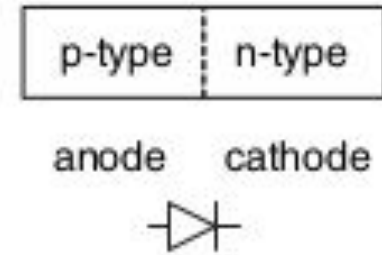
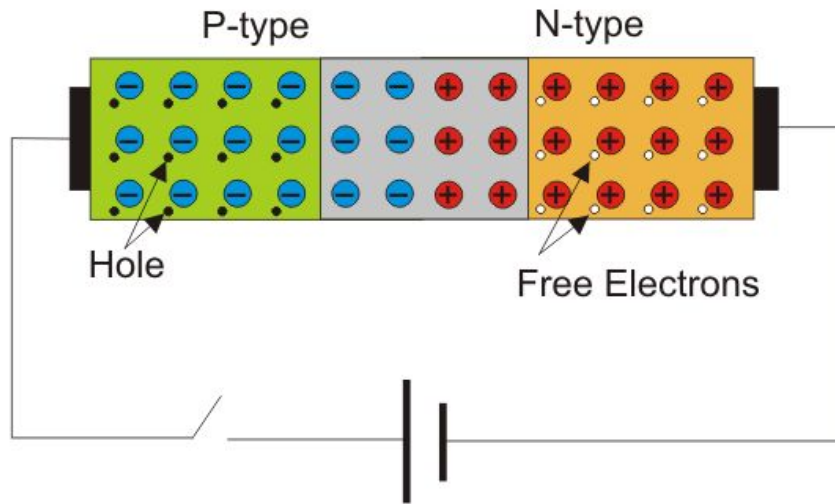


Yarıiletkenler

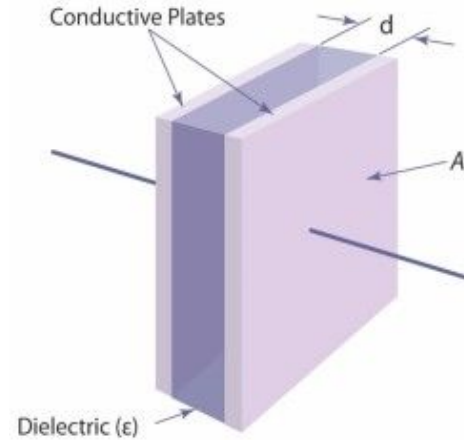
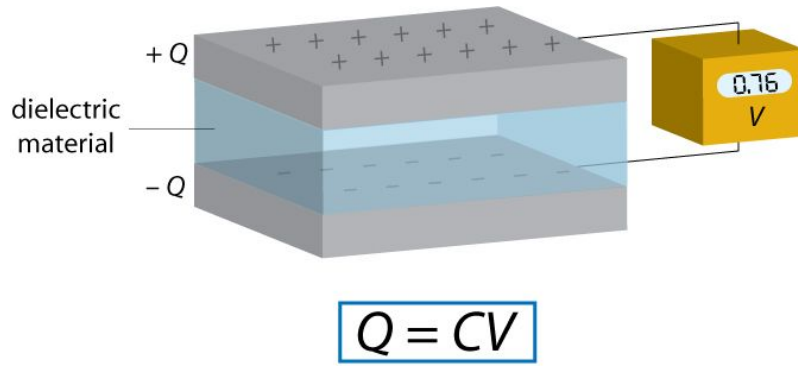
Doping in Semiconductors



Diyod



Kondansatör

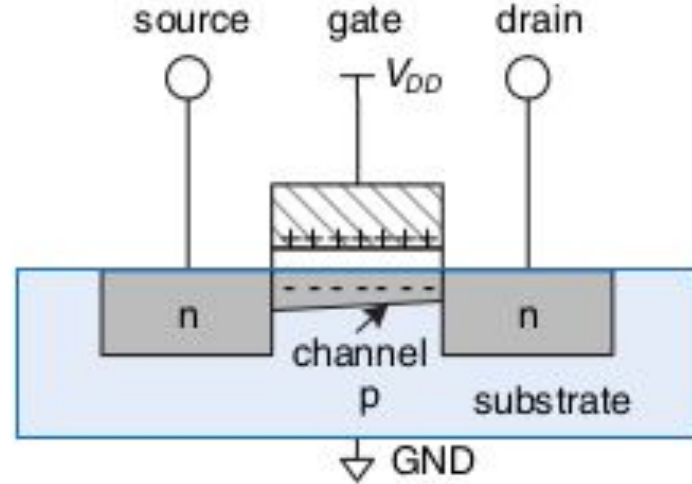
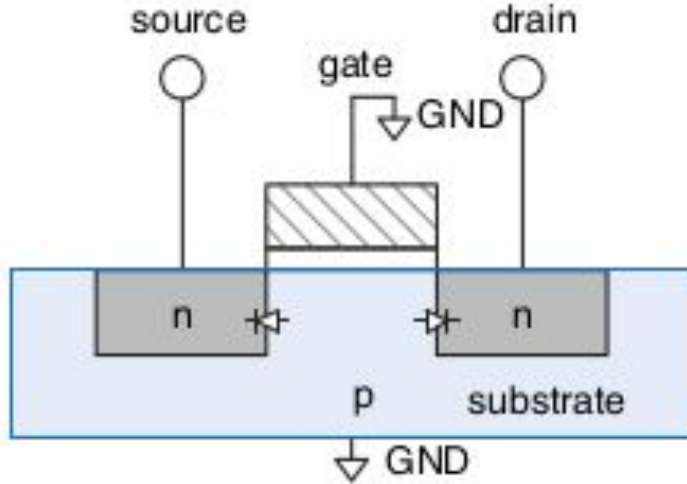


$$\text{Capacitance (C)} = \frac{\epsilon A}{d}$$

ϵ = permittivity of dielectric
 A = overlapping area of plates
 d = distance between plates

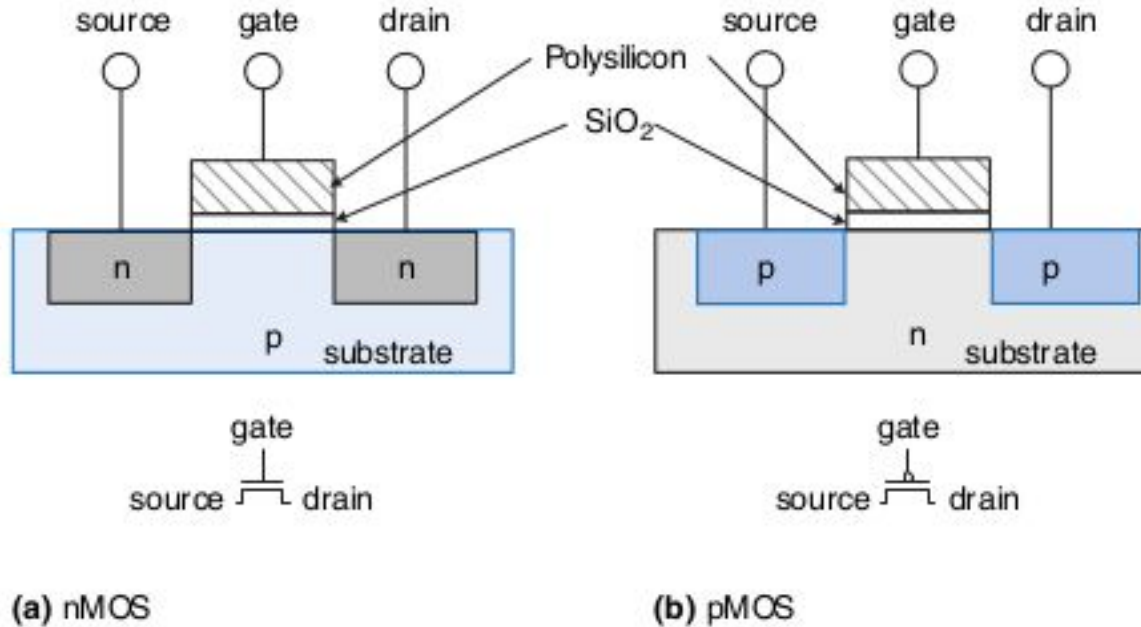
<https://www.youtube>

MOSFET (nMOS & pMOS)



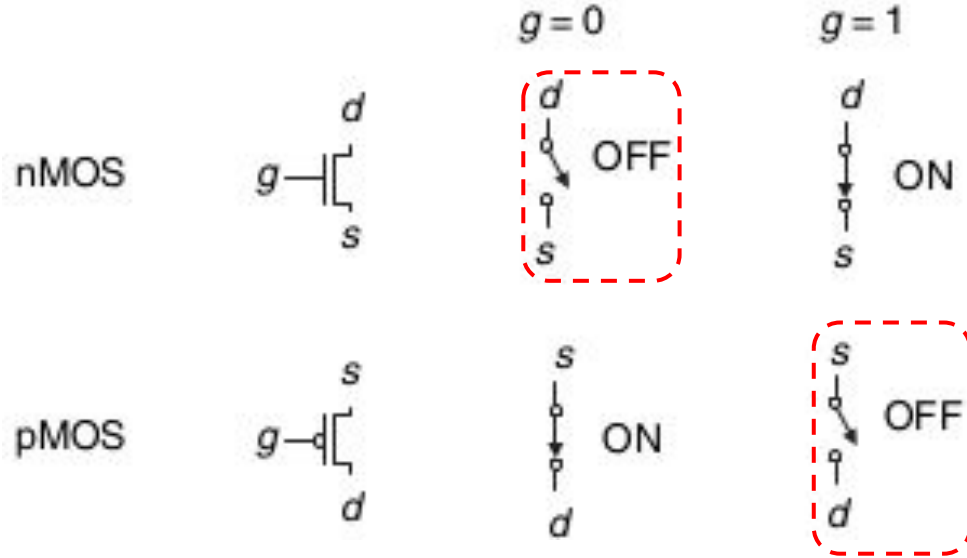
<https://www.youtube.com/watch?v=stM8dgcY1CA>

MOSFET (nMOS & pMOS)



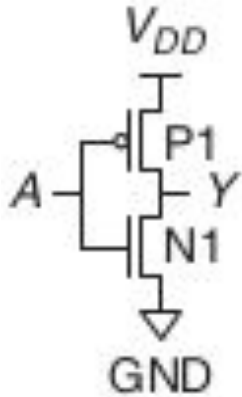
<https://www.youtube.com/watch?v=aCOyq4YzBtY>

MOSFET (nMOS & pMOS)



CMOS(Complementary MOS) Not Kapısı

NOT

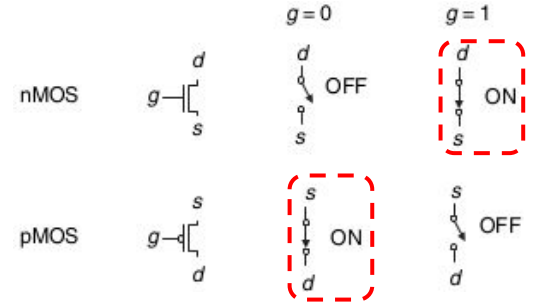


N1 \rightarrow NMOS

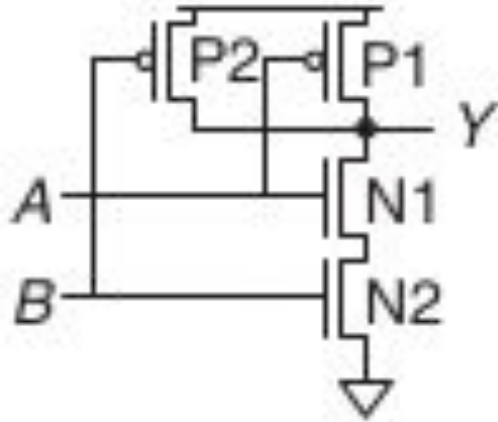
P1 \rightarrow PMOS

A=0 \rightarrow NMOS = OFF & PMOS= ON
Y = VDD (logic 1)

A=1 \rightarrow NMOS = ON & PMOS= OFF
Y = GND (logic 0)

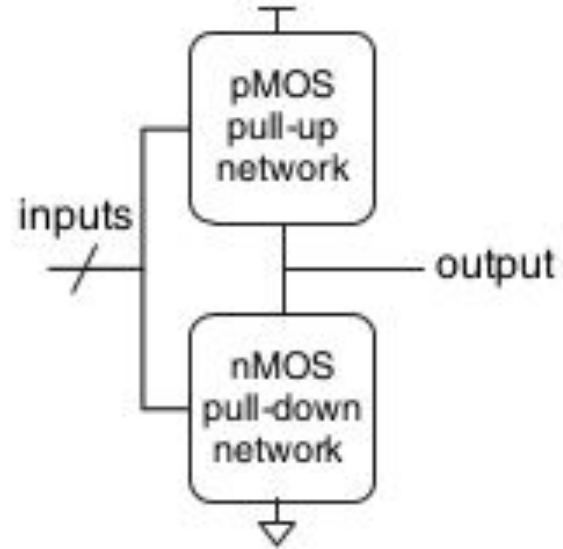
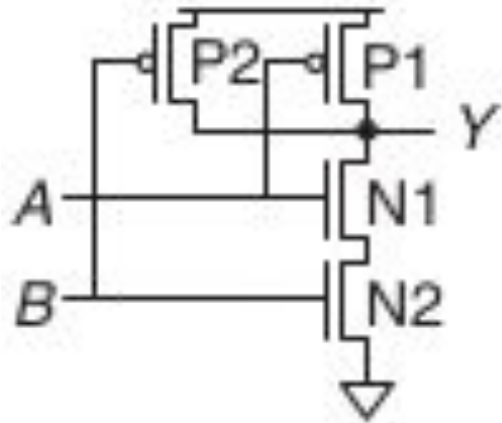


Two-input NAND gate



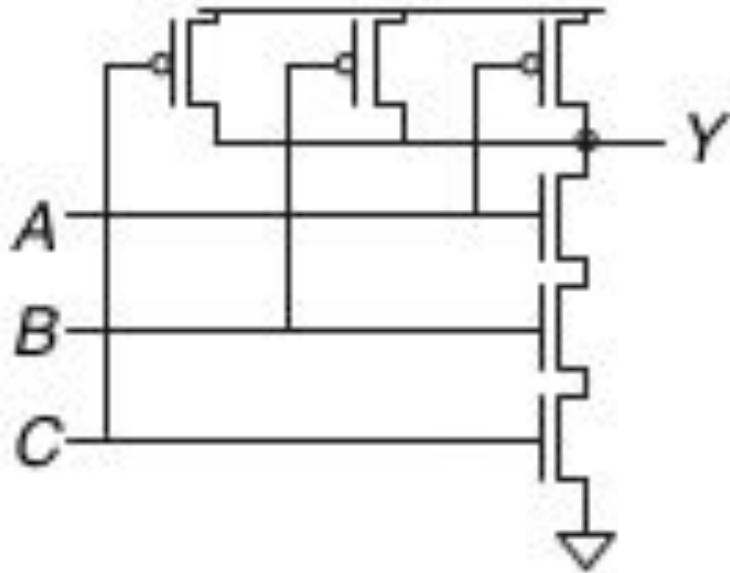
A	B	Pull-Down Network	Pull-Up Network	Y
0	0	OFF	ON	1
0	1	OFF	ON	1
1	0	OFF	ON	1
1	1	ON	OFF	0

Two-input NAND gate

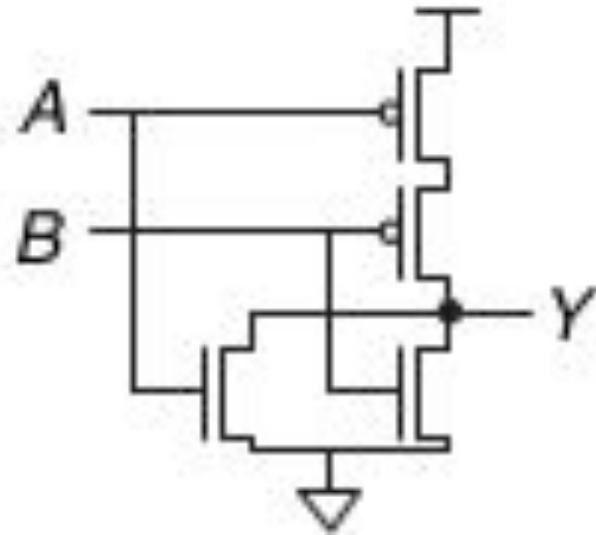


THREE-INPUT NAND SCHEMATIC

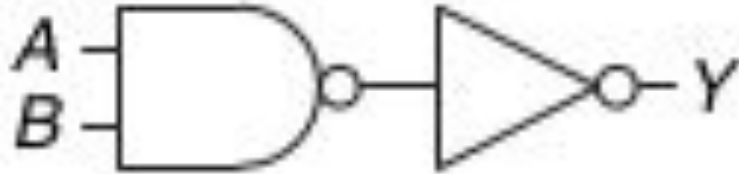
NAND



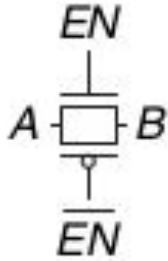
NOR



TWO-INPUT AND SCHEMATIC

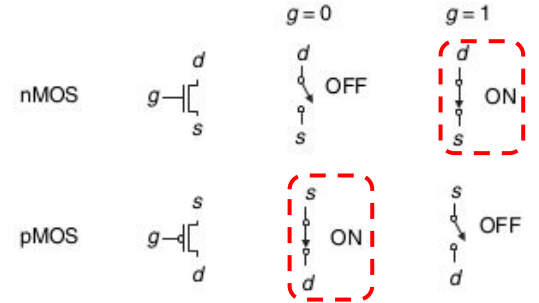


Transmission Gates



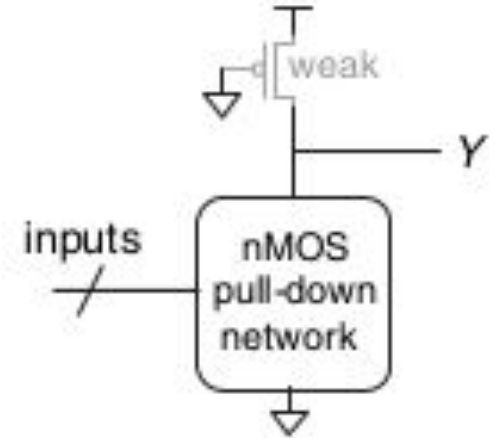
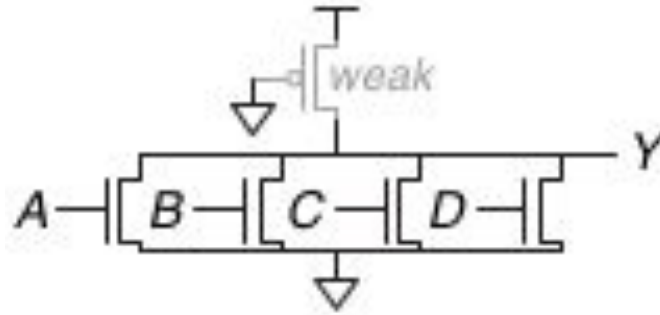
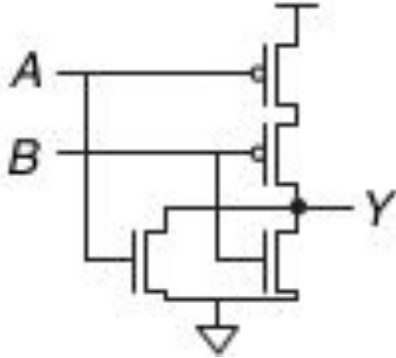
$EN=0 \ \& \ EN'=1 \rightarrow \text{nMOS,pMOS OFF}$

$EN=1 \ \& \ EN'=0 \rightarrow \text{nMOS,pMOS ON}$



Pseudo-nMOS Logic

NOR



Seri bağlı devre elemanları paralel bağlı devre elemanlarına göre daha yavastırlar.
pMOS transistörler nMOS transistörlere göre daha yavaştır.

Güç Tüketimi(Aktif/Pasif Güç)

6 watt saatlik (W-hr) bataryaya sahip bir cep telefonu 1,2 V'da çalışsın;

Aktif kullanıldığı durumda;

Frakansı: 300 MHz

Yonga içindeki ortalama kapasitans miktarı: 10 nF (10^{-8} Farads)

Anten gücü: 3 W

Batarya ömrü: ?

$$P_{\text{dynamic}} = \frac{1}{2} C V_{DD}^2 f$$

Aktif kullanılmadığı durumda;

Dinamik güç: Yaklaşık 0

Sakin Akım: 40 mA

Batarya ömrü: ?

$$P_{\text{static}} = I_{DD} V_{DD}$$

Güç Tüketimi

6 watt saatlik (W-hr) bataryaya sahip bir cep telefonu 1,2 V'da çalışsın;

Aktif kullanıldığı durumda;

$$P_{\text{static}} = (0.040 \text{ A})(1.2 \text{ V}) = 48 \text{ mW}$$

$$\text{Bateri ömrü} = 6 (\text{Whr}) / (0.048 \text{ W}) = 125 \text{ saat (Yaklaşık 5 gün)}$$

Aktif kullanıldığı durumda;

$$P_{\text{dynamic}} = (0.5)(10^{-8} \text{ F})(1.2 \text{ V})^2 (3 \times 10^8 \text{ Hz}) = 2.16 \text{ W}$$

$$\text{Toplam güç: } 2.16 \text{ W} + 0.048 \text{ W} + 3 \text{ W} = 5.2 \text{ W}$$

$$\text{Bateri ömrü} = 6 \text{ Whr} / 5.2 \text{ W} = 1.15 \text{ saat}$$

$$P_{\text{dynamic}} = \frac{1}{2} C V_{DD}^2 f$$

$$P_{\text{static}} = I_{DD} V_{DD}$$

Sorular

